

## P-Channel 20-V (D-S) MOSFET

## **Description**

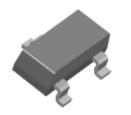
These miniature surface mount MOSFETs utilize High Cell Density process. Low rDS(on) assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

#### **Features**

- Low rDS(on) provides higher efficiency and extends battery life
- · High power and current handling capability
- · Low side high current DC-DC Converter
- Applications
- Miniature SOT-23 Surface Mount Package
- · Saves Board Space
- · RoHS compliant package

## **Packing & Order Information**

3,000/Reel

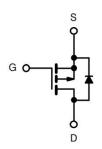


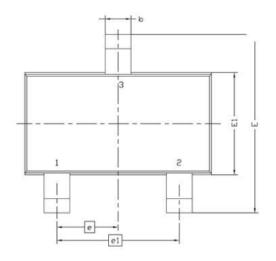
RoHS COMPLIANT

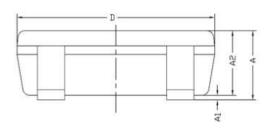


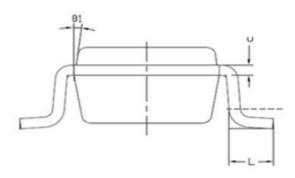
**ESD Protected** 

### **Graphic symbol**









Cumbal	MILLIMET	TERS
Symbol	MIN	MAX
Α	0.8	1.2
A1	0	0.1
A2	0.7	1.1
b	0.3	0.5
С	0.1	0.2
D	2.7	3.1
E	2.6	3
E1	1.4	1.8
е	0.95	BSC
e1	1.9 BSC	
Les	0.3	0.6
θ1	7° N	MON



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## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (T <sub>A</sub> =25°C unless otherwise specified)						
Symbol	Parameter	Value	Unit			
$V_{DS}$	Drain-Source Voltage	20	V			
V <sub>GS</sub>	Gate-Source Voltage	±20	V			
	Continuous Drain Current <sup>a</sup> (T <sub>A</sub> = 25°C)	4.0	Α			
I <sub>D</sub>	Continuous Drain Current <sub>a</sub> (T <sub>A</sub> =70°C)	3.1	Α			
I <sub>DM</sub>	Pulsed Drain Current <sup>b</sup>	±20	Α			
Is	Continuous Source Current (Diode Conduction) <sup>a</sup>	1.6	А			
T <sub>J</sub> /T <sub>STG</sub>	Operating Junction and Storage Temperature	-55 to +150	°C			
P <sub>D</sub>	Power Dissipation <sup>a</sup> (T <sub>A</sub> =25°C)	1.3	W			
	Power Dissipation <sup>a</sup> (T <sub>A</sub> =70°C)	0.8	W			

Thermal Resistance Ratings						
Symbol	Parameter	Maximum	Units			
R <sub>THJA</sub>	Maximum Junction-to-Ambient <sup>a</sup> (t <= 5 sec)	100	°C/W			
	Maximum Junction-to-Ambient <sup>a</sup> (Steady-State)	166	C/VV			

#### Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Static						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
$V_{GS(th)}$	Gate-Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	0.7			V
I <sub>GSS</sub>	Gate-Body Leakage	$V_{DS}$ =0 V , $V_{GS}$ = ±8 V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 16 V , V <sub>GS</sub> = 0 V V <sub>DS</sub> = 16 V , V <sub>GS</sub> = 0 V , T <sub>J</sub> = 55°C			1 10	uA
I <sub>D(on)</sub>	On-State Drain Current <sup>A</sup>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			Α
I <sub>DS(on)</sub>	Drain-Source On-Resistance <sup>A</sup>	$V_{GS} = 4.5 \text{ V}, I_D = 4.6 \text{ A}$ $V_{GS} = 2.5 \text{ V}, I_D = 3.9 \text{ A}$			32 44	mΩ
g <sub>fs</sub>	Forward Tranconductance <sup>A</sup>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 4.0 A		11.3		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> = 1.6 A , V <sub>GS</sub> = 0 V		0.75		V

Dynamic <sup>b</sup>							
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units	
$Q_g$	Total Gate Charge	$V_{DS} = 10 \text{ V}, I_{D} = 4.0 \text{ A},$ $V_{GS} = 4.5 \text{ V}$		13.4		nC	
Q <sub>gs</sub>	Gate-Source Charge			0.9		nC	
$Q_{gd}$	Gate-Drain Charge			2.0		nC	



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Dynamic <sup>b</sup>							
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, R_L = 15 \Omega,$ $V_{GEN} = 4.5 \text{ V}, I_D = 5 \text{ A}$		8		ns	
t <sub>r</sub>	Rise Time			24		ns	
t <sub>d(off)</sub>	Turn-Off Delay Time			35		ns	
t <sub>f</sub>	Fall Time			10		ns	
t <sub>rr</sub>	Source-Ddrain Reverse Recovery Time	I <sub>F</sub> = 1.6 A , di/dt=100 A/uS		40		ns	

## Notes:

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.



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